
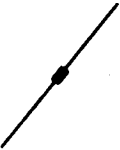






Schottky Rectifiers

SWITCHMODE Schottky Power Rectifiers with the high speed and low forward voltage drop characteristic of Schottky's metal/silicon junctions are produced with ruggedness and temperature performance comparable to silicon-junction rectifiers. Ideal for use in low voltage, high frequency power supplies and as very fast clamping diodes, these devices feature switching times less than 10 ns, and are offered in current ranges from 0.5 to 300 amperes, and reverse voltages up to 60 volts.

In some current ranges, devices are available with junction temperature specifications of 125°C, 150°C, 175°C. Devices with higher T_J ratings can have significantly lower leakage currents, but higher forward-voltage specifications. These parameter tradeoffs should be considered when selecting devices for applications that can be satisfied by more than one device type number. Detailed specifications are available on the individual data sheets.

	I_O, AVERAGE FORWARD RECTIFIED CURRENT (A)							
	0.5	1	3		8	7	10	15
CASE	299-02 Glass	59-04 Plastic	267 Plastic		60 Metal	221B-01 Plastic		221A-02 Plastic
V _{RRM}	 (00-35) 00-204AH				 **	 TO220AC		 TO220AB*
20		1N5817	1N5820	MBR320	BYS08-20			
30	MBR030	1N5818	1N5821	MBR330	BYS08-30			
35						MBR735	MBR1035	MBR1535CT
40	MBR040	1N5819	1N5822	MBR340				
45					BYS08-45	MBR745	MBR1045	MBR1545CT
50, 60				MBR350/360	BYS08-50		MBR1060	
IFSM(A)	5.0	25	80	80	400	150	150	150
T _J or T _C at rated I _O (°C)	75	90	95	90	100	105	135	105
T _J MAX.	150	125	125	150	150	150	150	150
BARRIER METAL	PLATINUM	CHROME		PLATINUM	CHROME	PLATINUM		
V _F MAX. at I _O (V)	.65	.60	.53	.60	.47	.57	.57	.72

(*) I_O is total device output.

(**) N° CECC 86 819 029.